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WHAT IS CLAIMED IS:

1. A damascene interconnection, comprising:

an interconnection trench formed in an insulating film and a pad trench
communicating therewith;
5 a protrusion formed by a portion not removed of said insulating film in said pad
trench to decrease a substantial opening area of said pad trench; and
trench to decrease a substantial opening area of said pad trench; and
a conductive film buried in said interconnection trench and said pad trench.

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2. A damascene interconnection according to claim 1, wherein said protrusion is

formed not to divide said conductive film buried in said pad trench.

10 3. A damascene interconnection according to claim 2, wherein said protrusion
increase a plurality of island protrusions distributed at a proper interval in said pad trench.

4. A damascene interconnection according to claim 2, wherein said protrusion
includes a ridge.

5. A damascene interconnection according to claim 1, wherein said protrusion is
15 formed to divide said conductive film buried in said pad trench.

6. A damascene interconnection according to claim 5, wherein said protrusion
includes a closed-loop ridge encompassing one part in said pad trench.

20 7. A damascene interconnection according to any of claims 1 to 6, further
comprising a contact hole formed in said pad trench and electrically connecting between
said conductive film and another conductive film arranged in a level lower than said
insulating film.

8. A semiconductor device, comprising:

25 a semiconductor substrate;

an insulating film formed on said semiconductor substrate;

an interconnection trench formed on said insulating film and communicating with

a semiconductor element;

a pad trench formed on said insulating film and communicating with said interconnection trench;

5 a protrusion formed by a portion of not removed of said insulating film in said pad trench and reducing a substantial opening area of said pad trench; and

a conductive film buried in said interconnection trench and said pad trench.

9. A semiconductor device according to claim 9, wherein said protrusion is formed not to divide said conductive film buried in said pad trench.

10. A semiconductor device according to claim 9, wherein said protrusion includes a plurality of island protrusions distributed at a proper interval in said pad trench.

11. A semiconductor device according to claim 9, wherein said protrusion includes a ridge.

12. A semiconductor device according to claim 8, wherein said protrusion is formed to divide said conductive film buried in said pad trench.

15 13. A semiconductor device according to claim 12, wherein said protrusion includes a closed-loop ridge encompassing one portion in said pad trench.

14. A semiconductor device according to any of claims 8 to 13, further comprising another conductive film formed in a level lower than said insulating film, and a contact hole formed through said insulating film in said pad trench and electrically connecting 20 between said conductive film and said other conductive film.